

FIG. 1

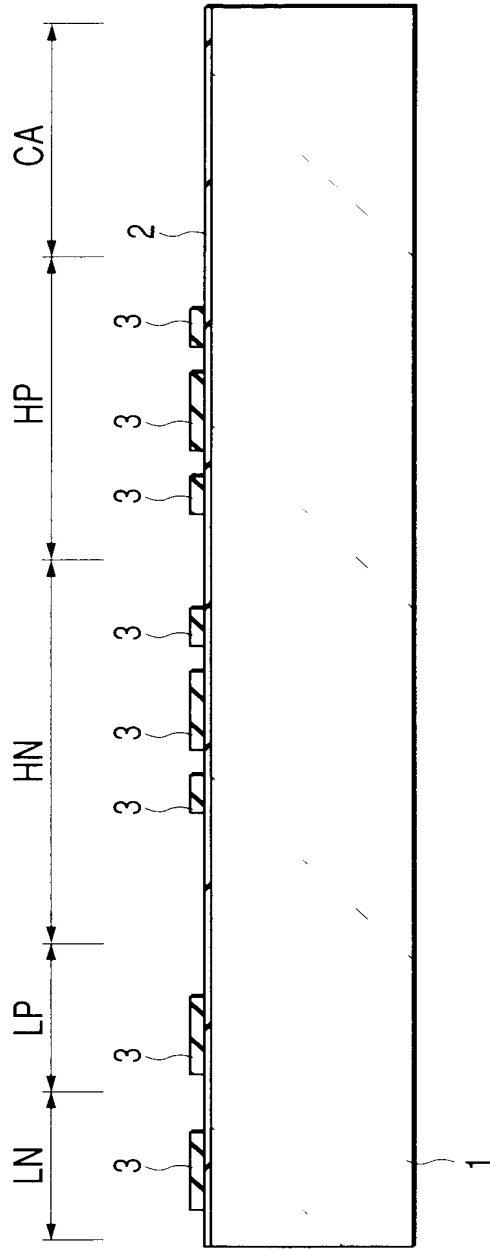
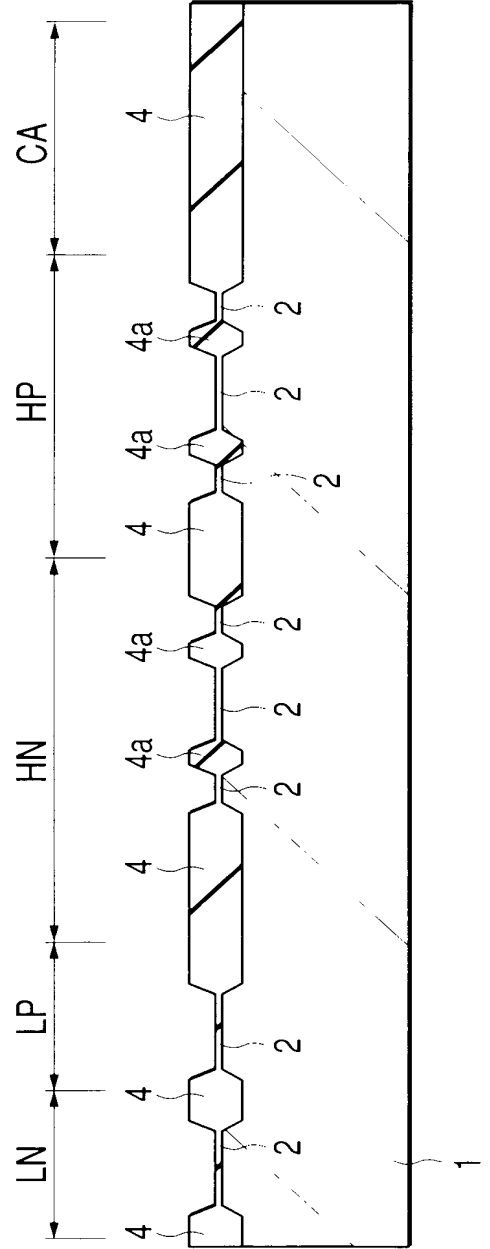
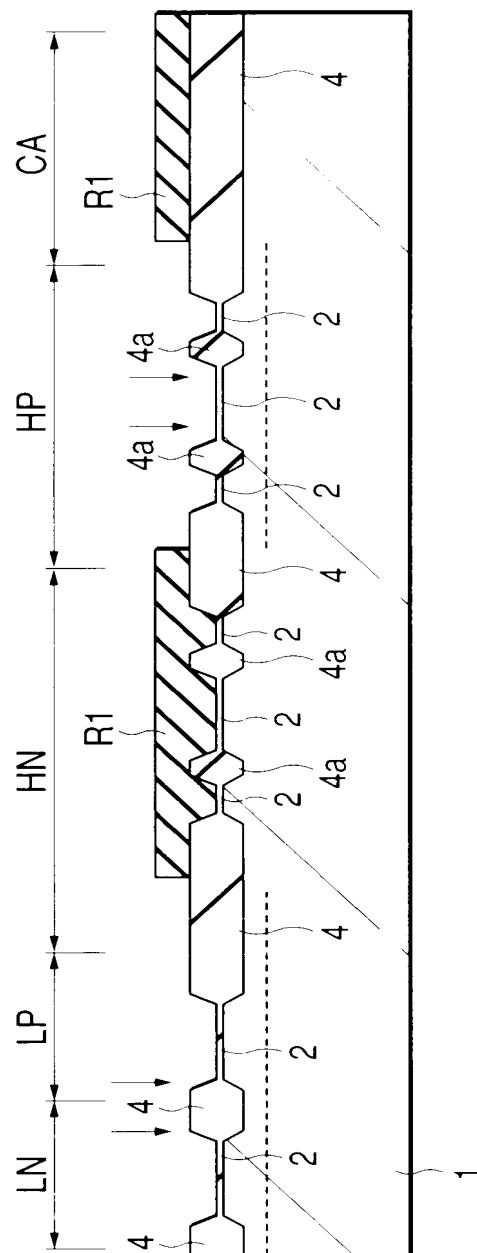


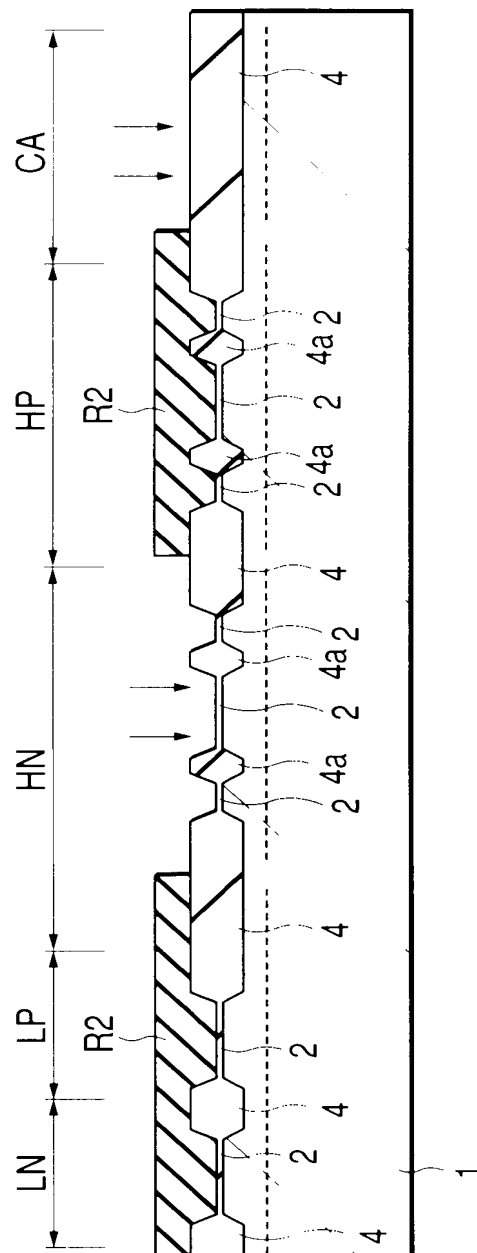
FIG. 2



**FIG. 3**

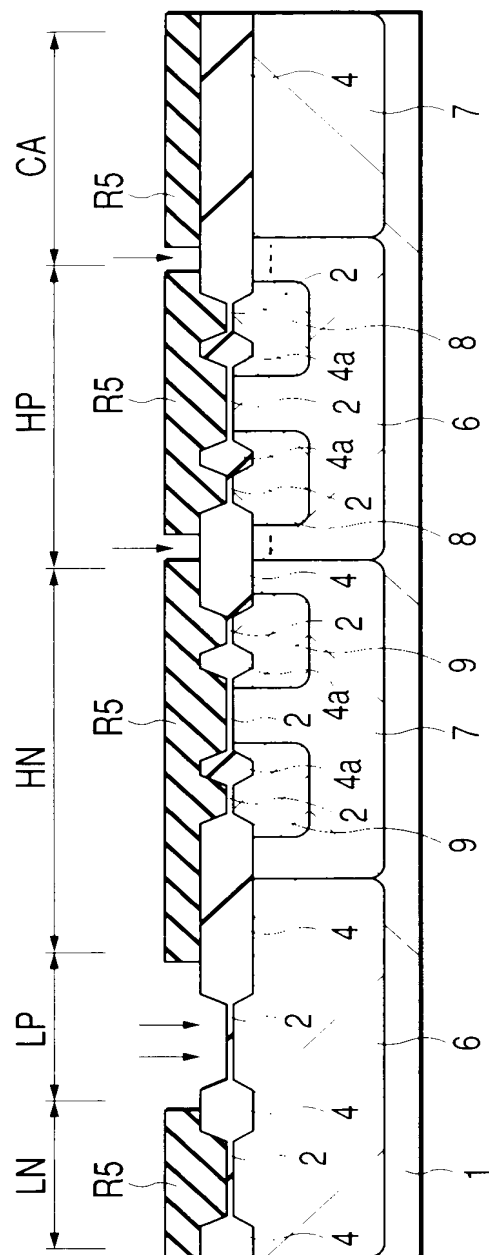


**FIG. 4**





**FIG. 7**



**FIG. 8**

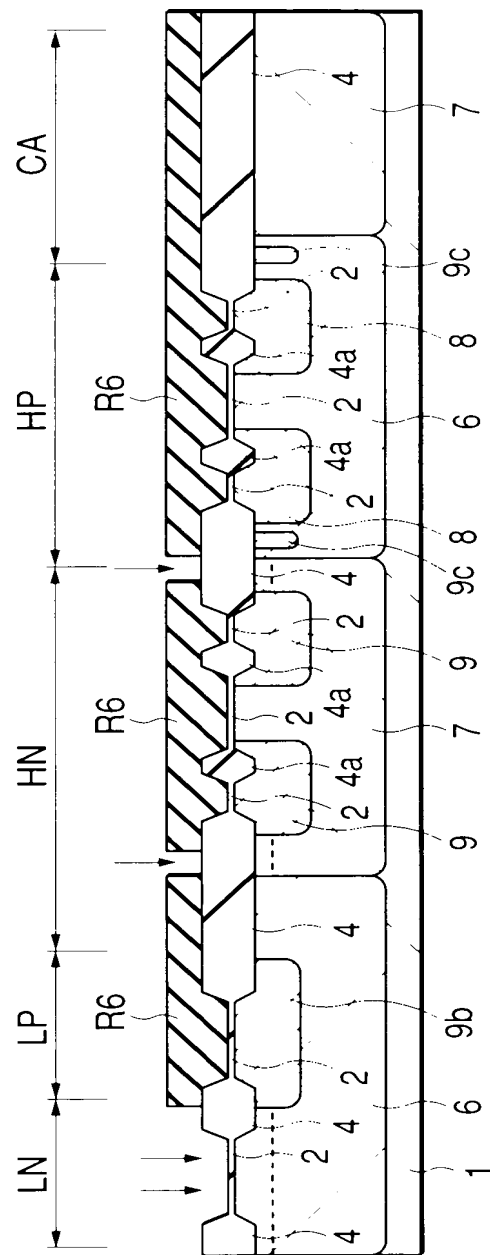


FIG. 9

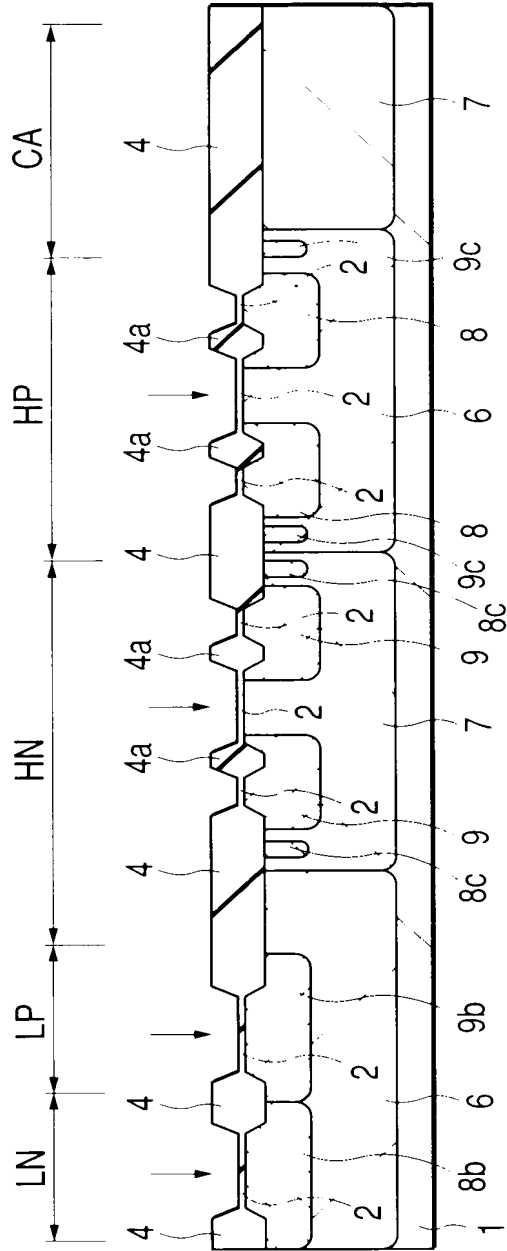


FIG. 10

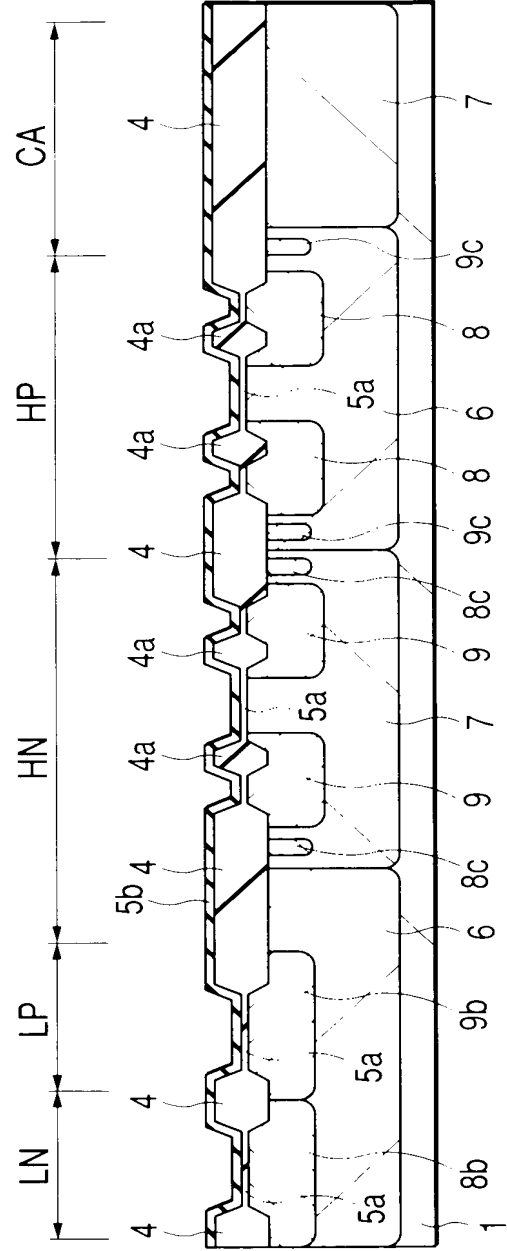


FIG. 11(a)

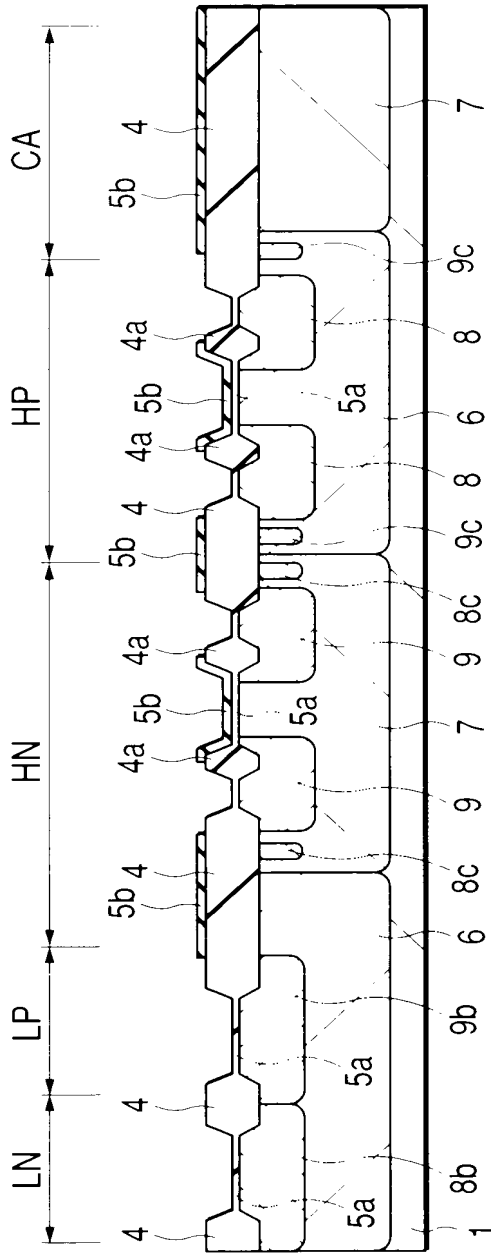
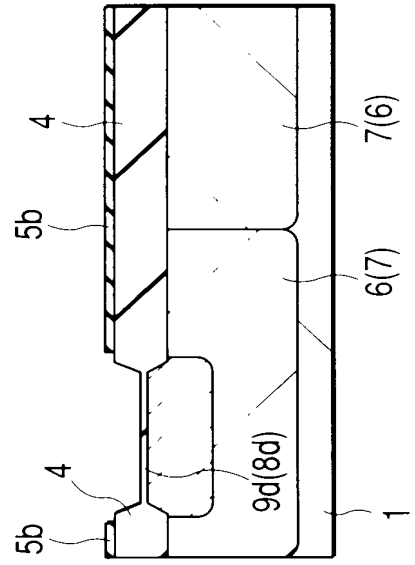


FIG. 11(b)



[illegible]

FIG. 14(a)

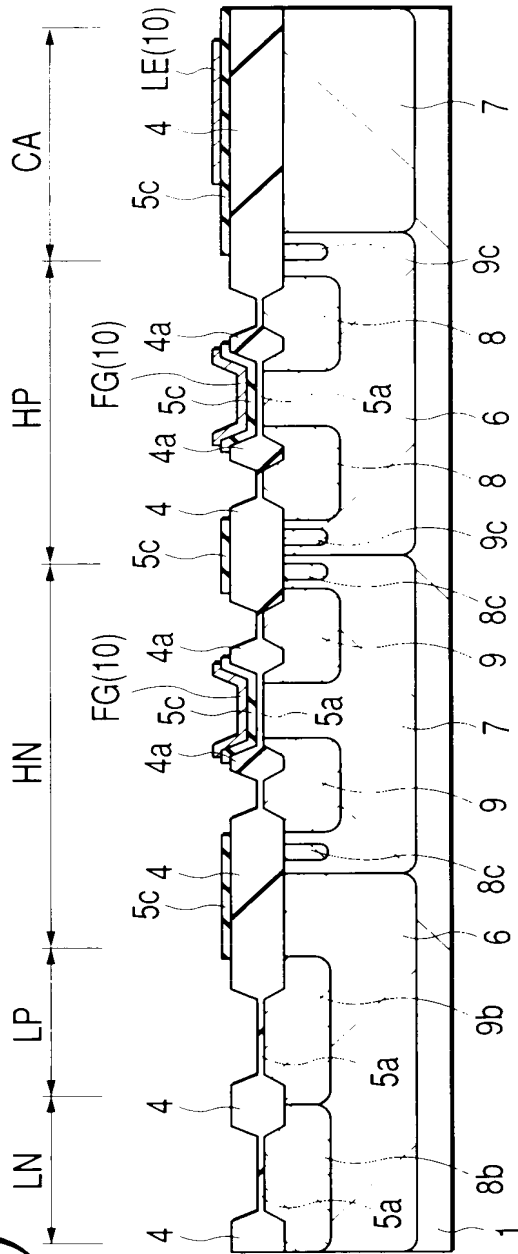


FIG. 14(b)

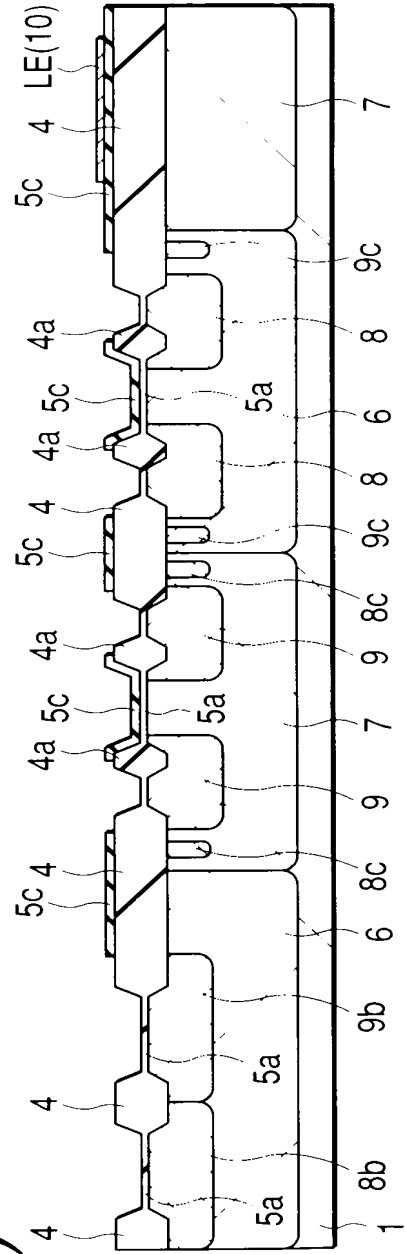




FIG. 15

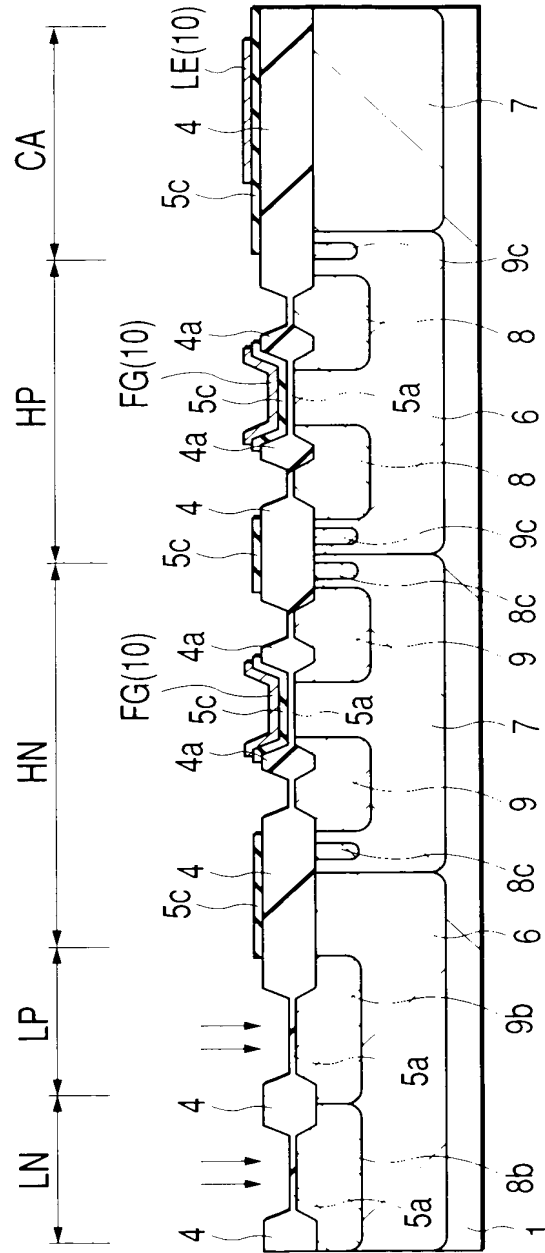


FIG. 16(a)

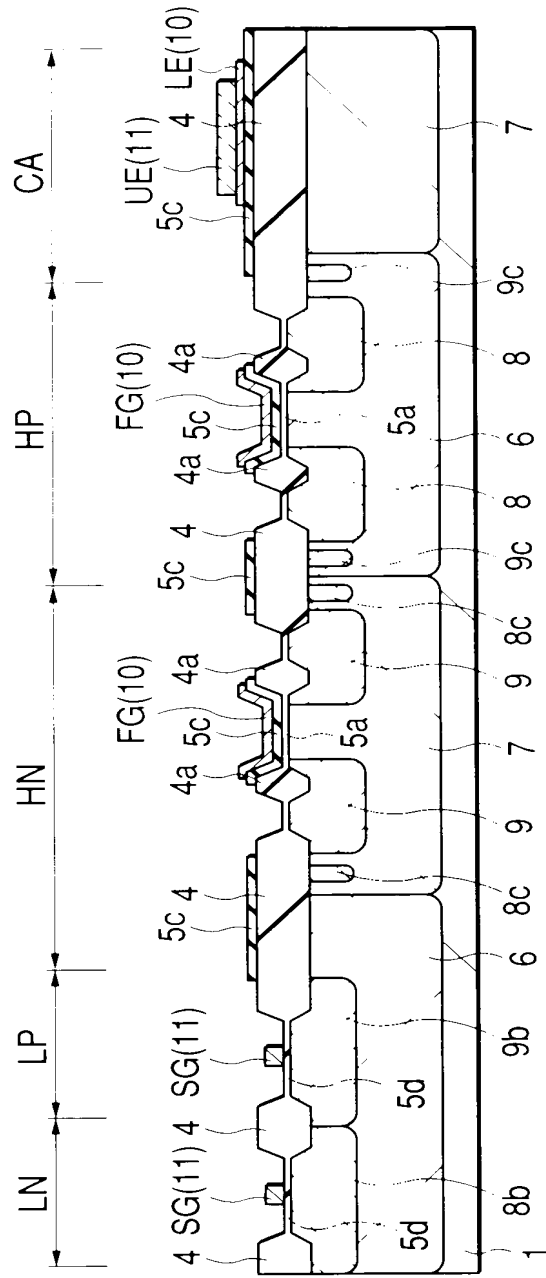


FIG. 16(b)

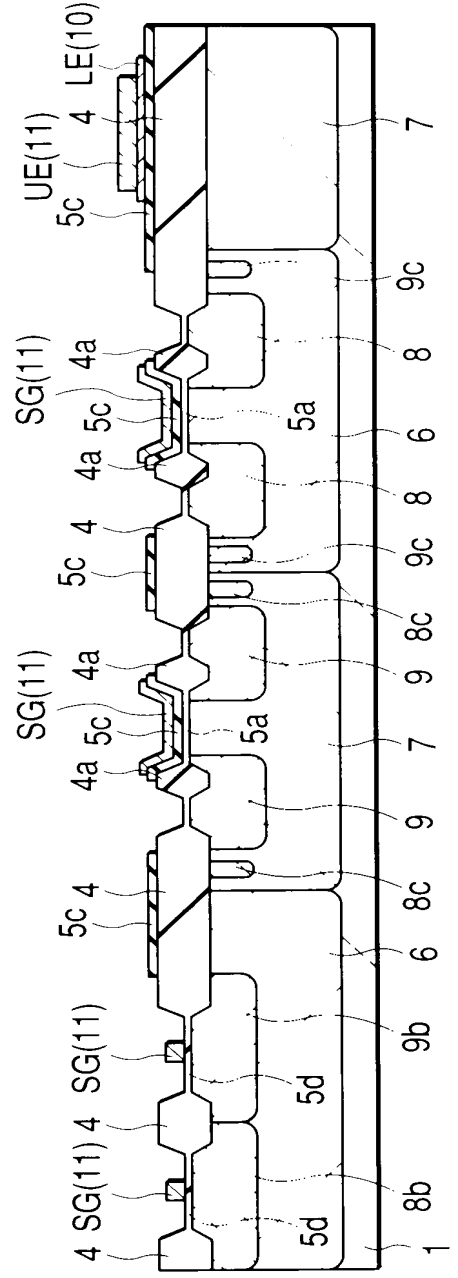


FIG. 17

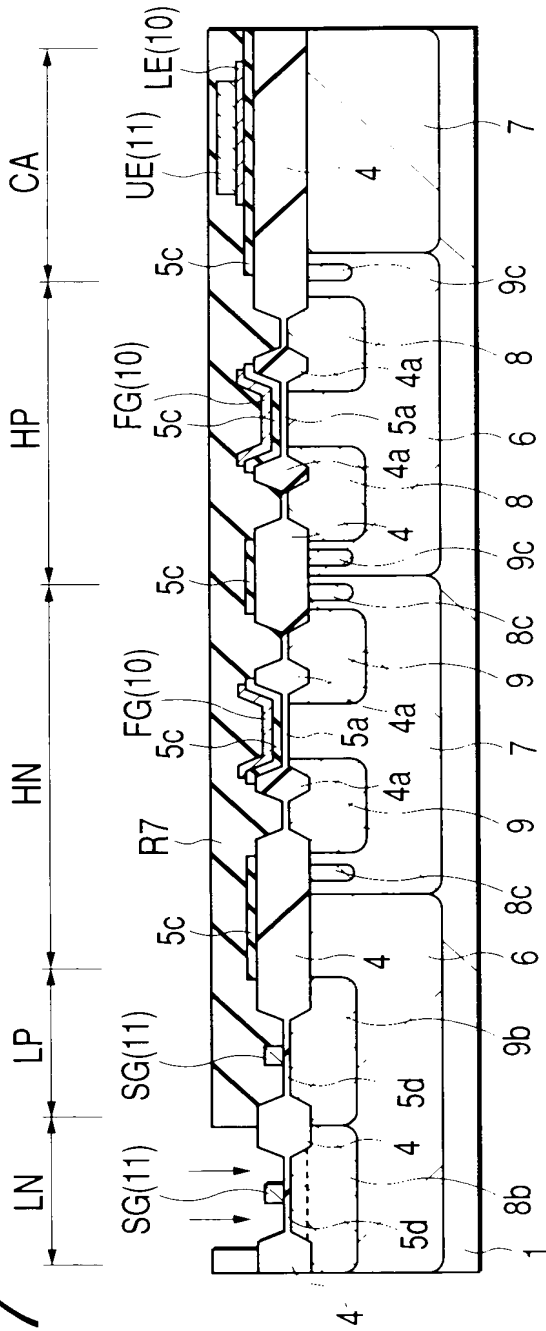


FIG. 18

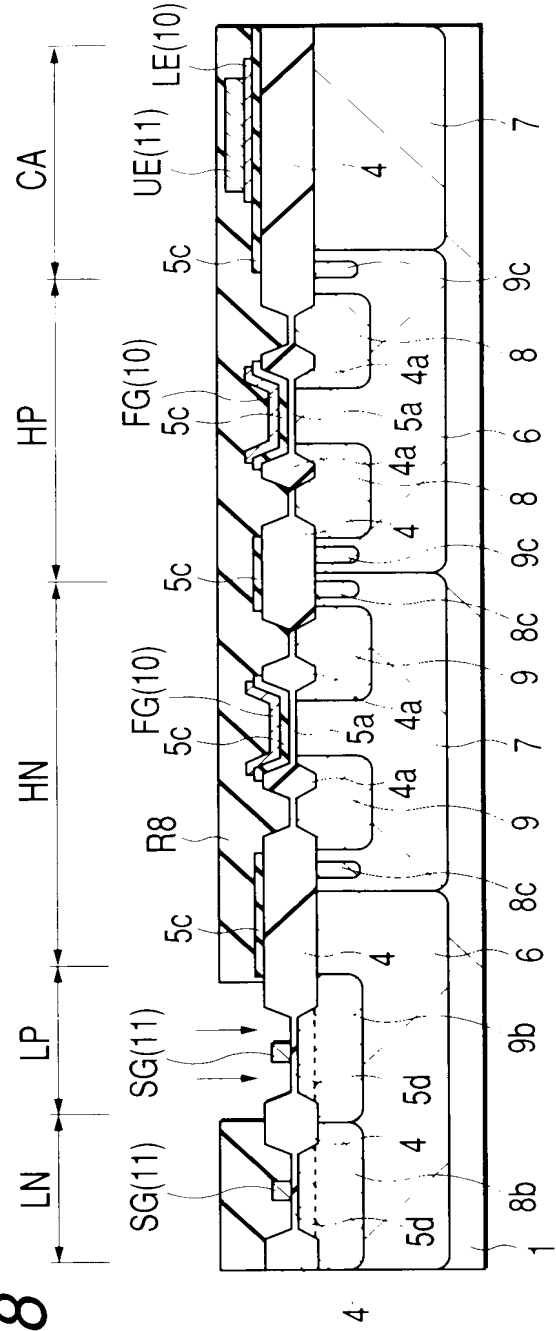




FIG. 21

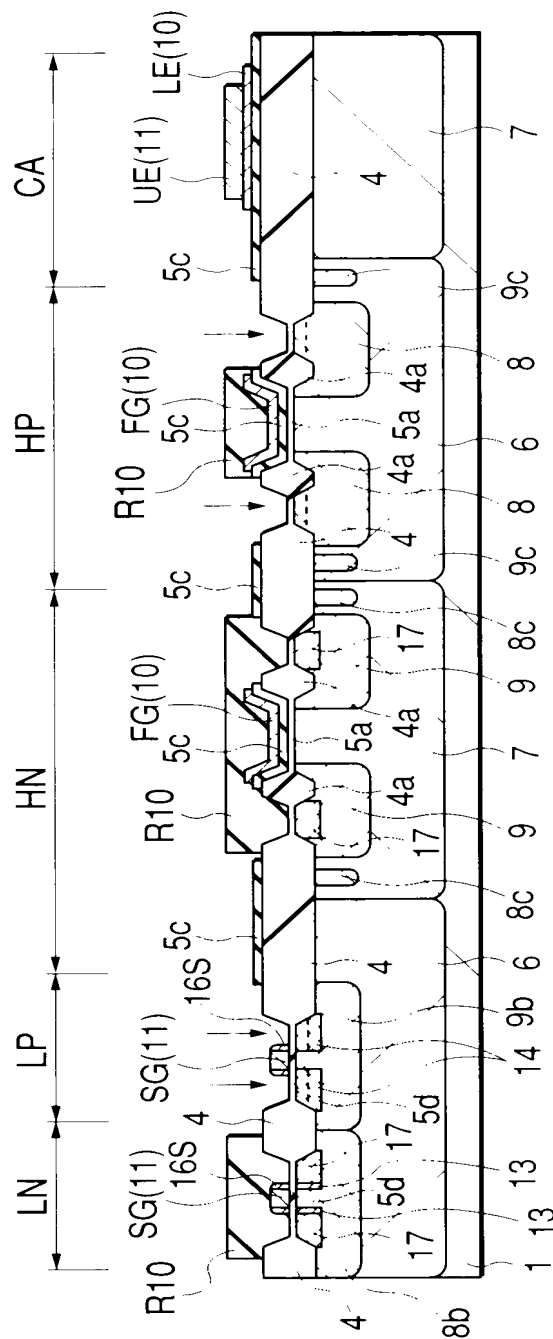


FIG. 22(a)

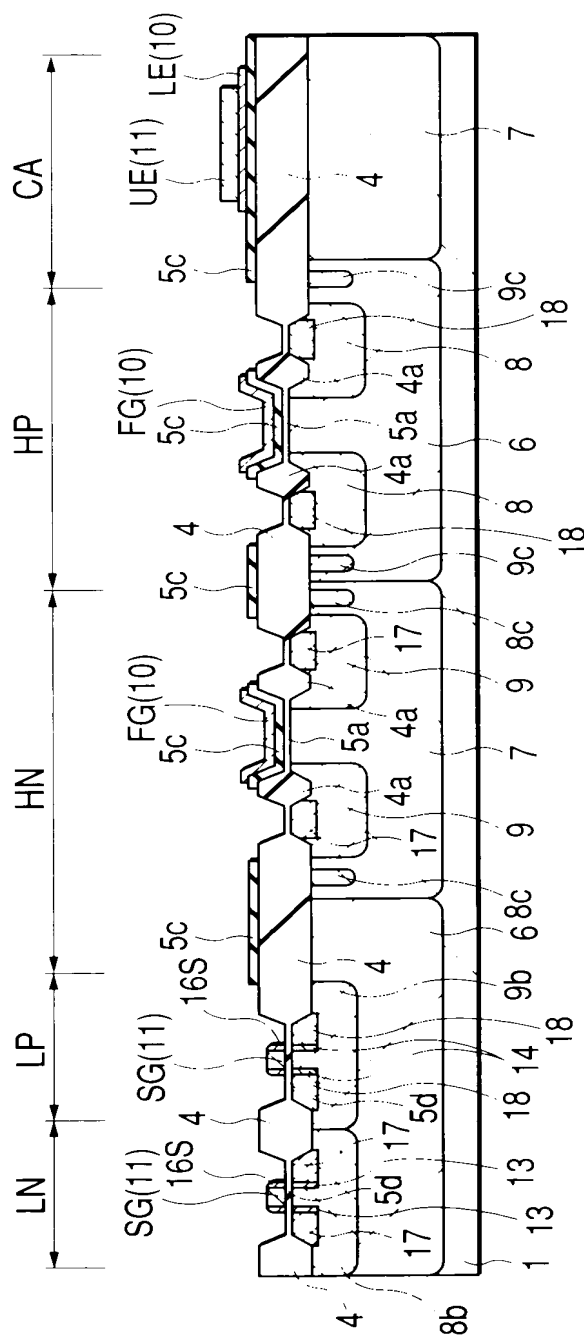


FIG. 22(b)

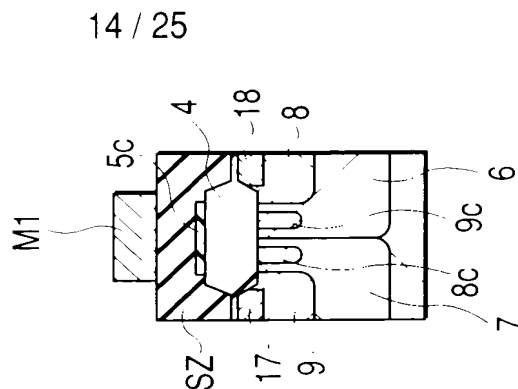


FIG. 23

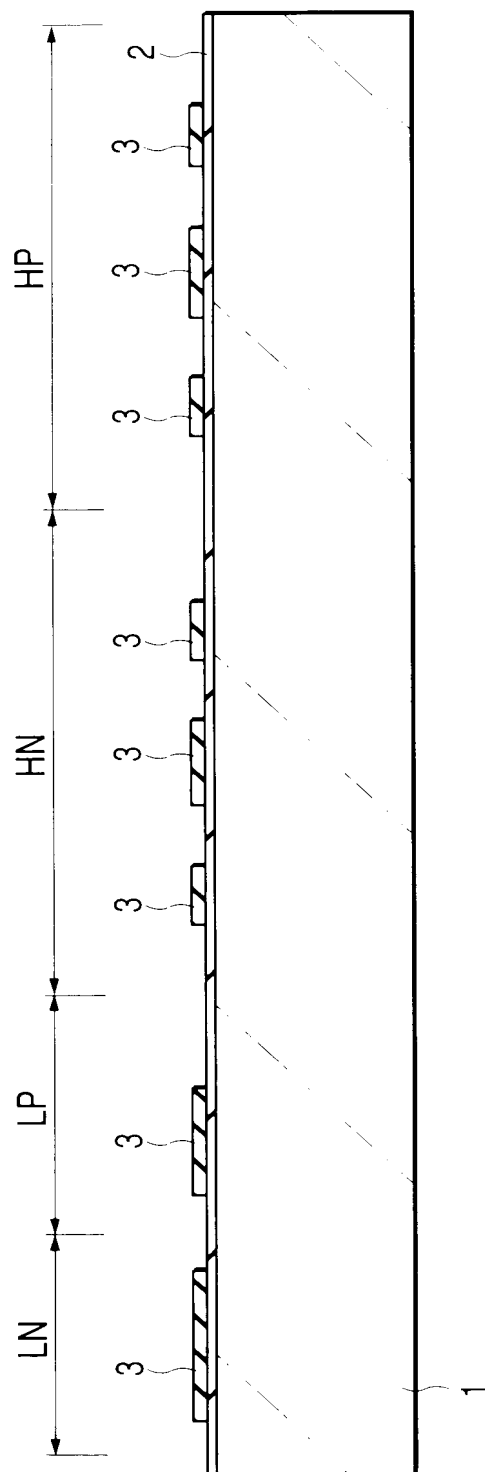


FIG. 24

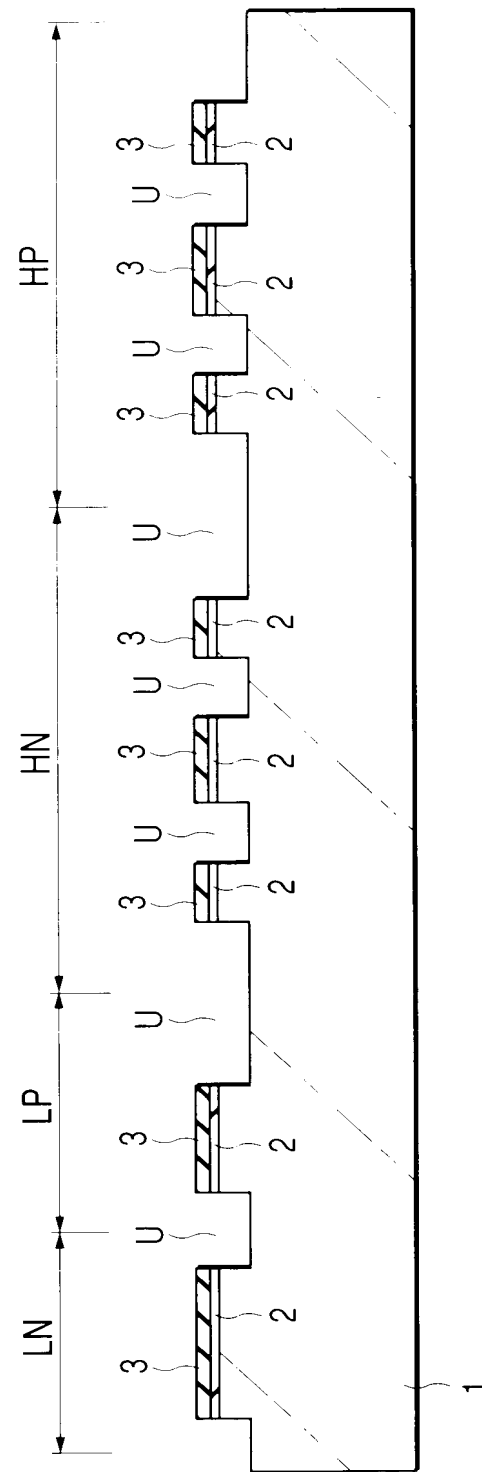


FIG. 25

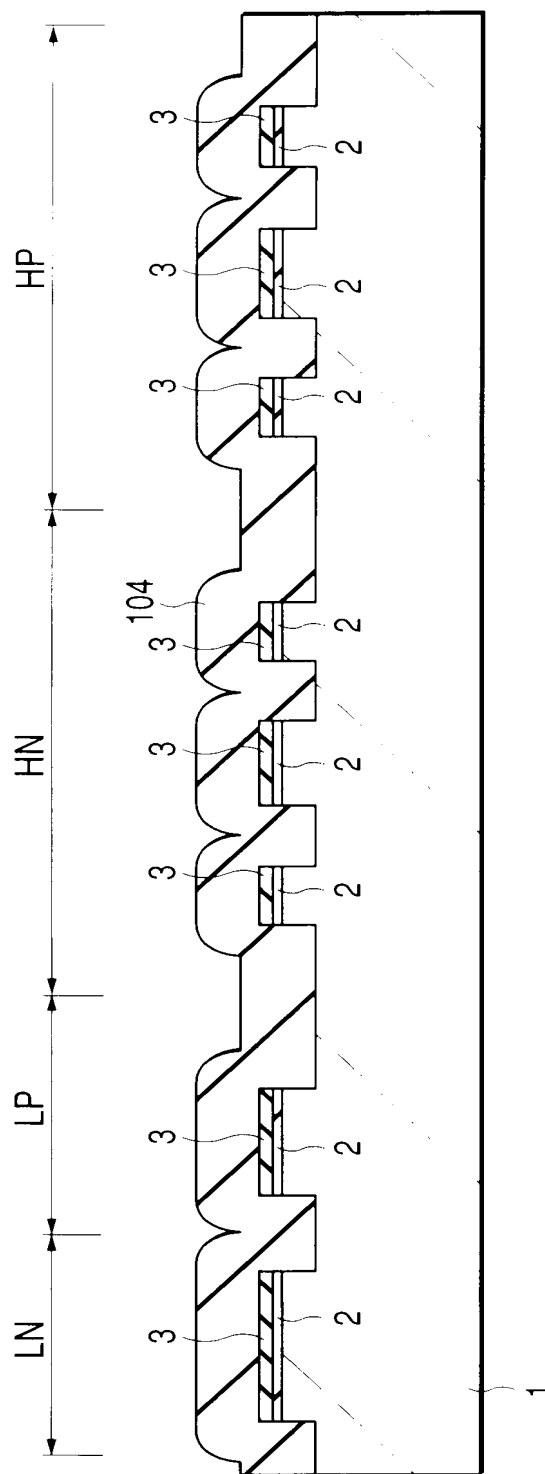




FIG. 26(a)

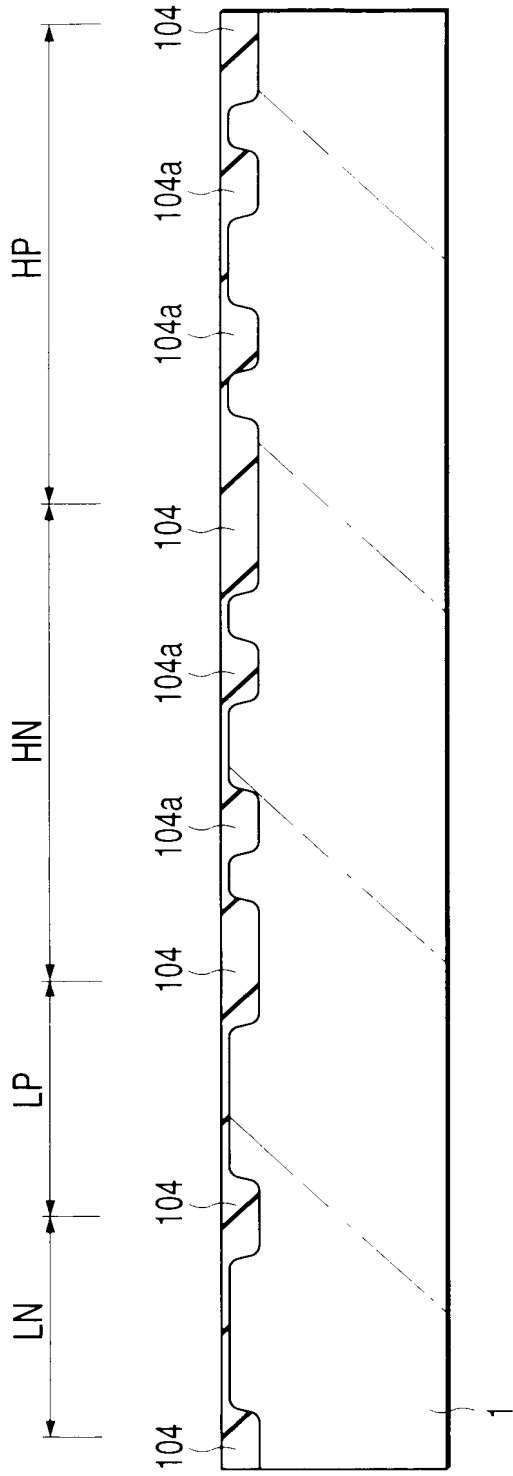


FIG. 26(b)

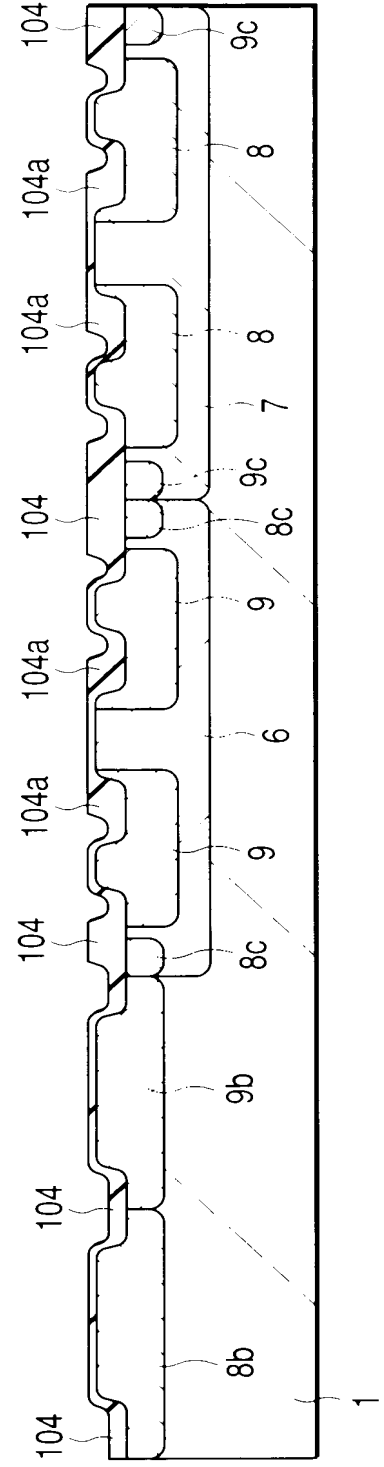


FIG. 27

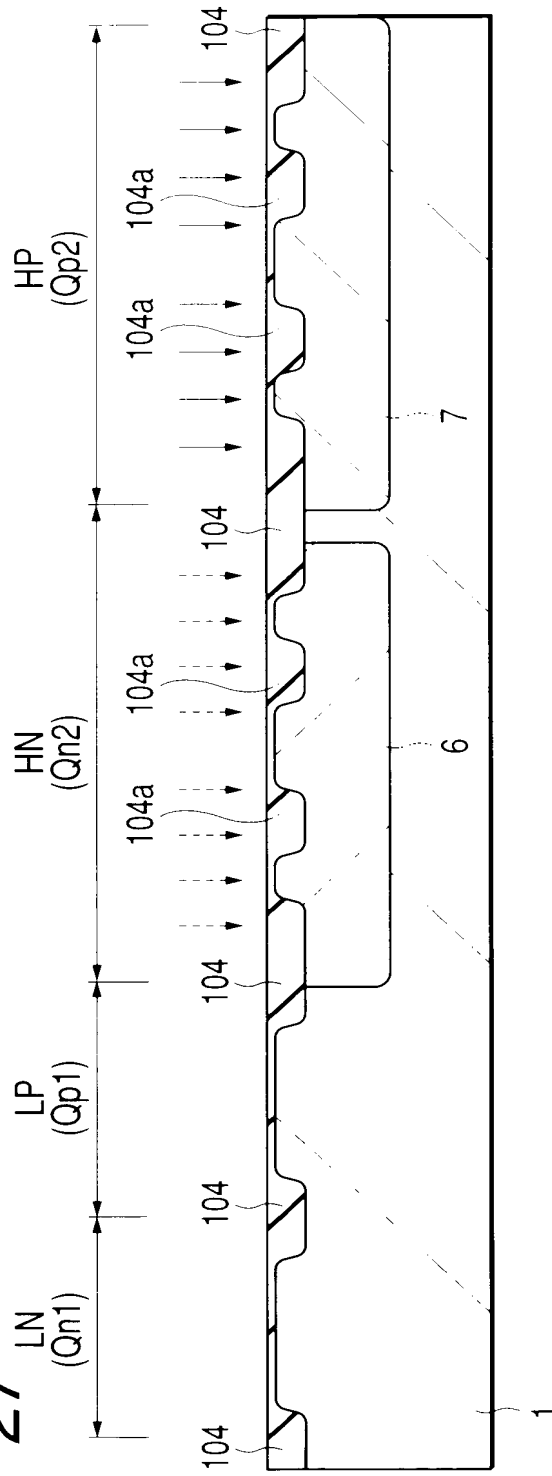
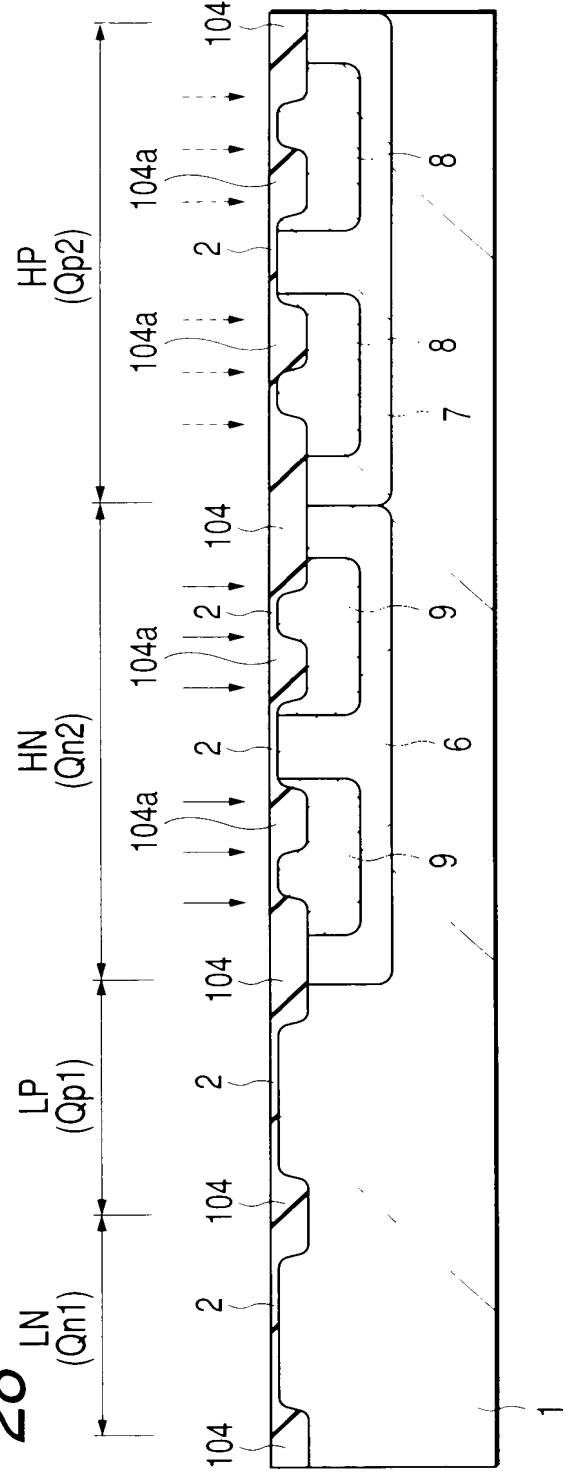
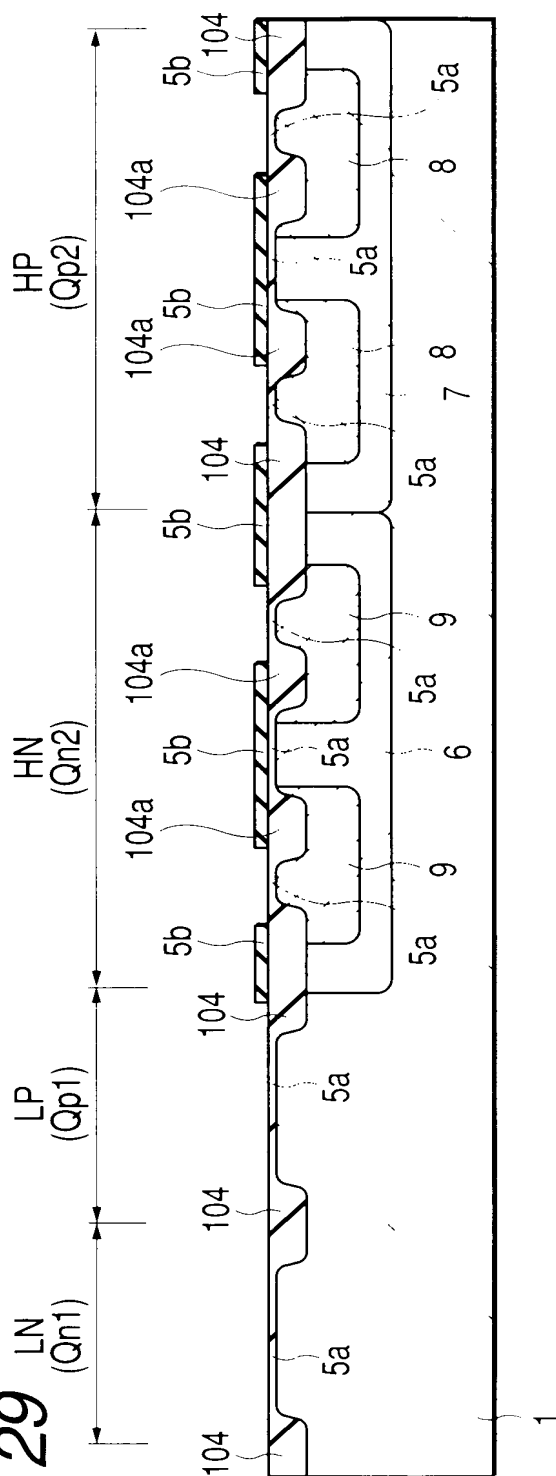


FIG. 28



**FIG. 29**  $^{LN}_{(Qn1)}$



**FIG. 30**  $\text{LN}_{(\text{Qn1})}$

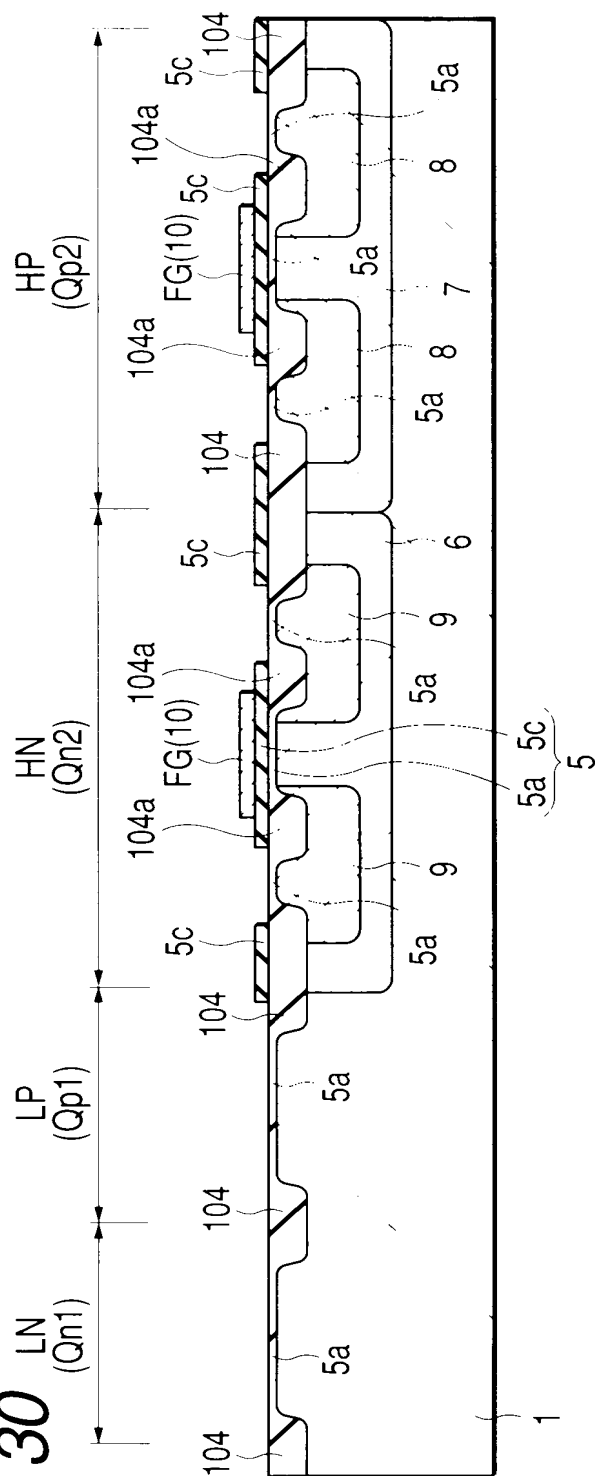


FIG. 31

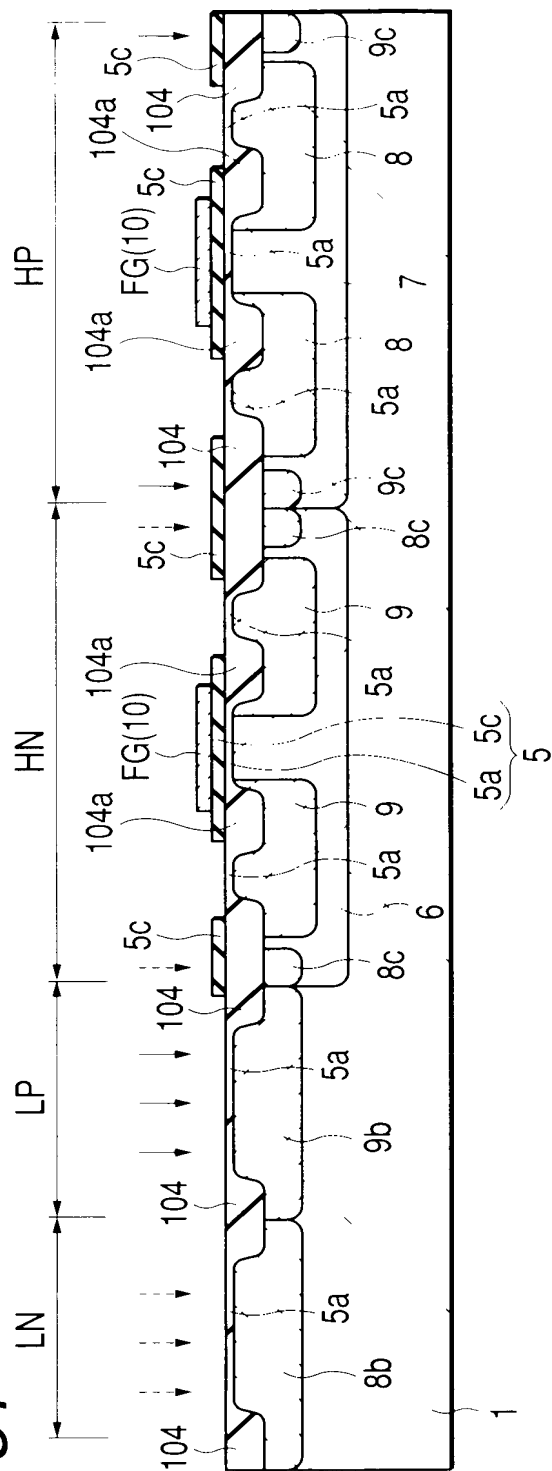
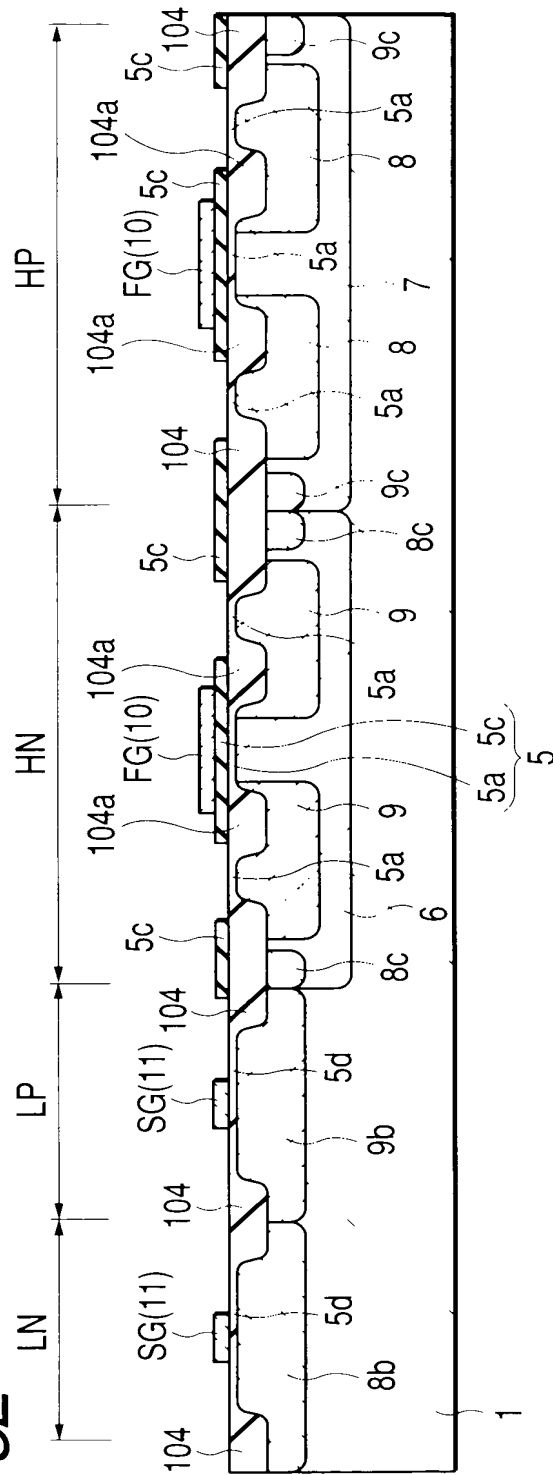


FIG. 32



This cross-sectional view shows a semiconductor device with a repeating structure of SG(11) and FG(10) regions. The device includes a substrate 1, a base layer 5a, and a series of layers 13, 14, 17, 18, 8b, 9b, 5d, 14, 18, 8c, 9, 17, 6, 17, 8c, 9c, 8, 18, 7, 8, 18, 9c. The SG(11) regions are labeled 15 and the FG(10) regions are labeled 15. The layers 104 and 16s are also indicated.

FIG. 34

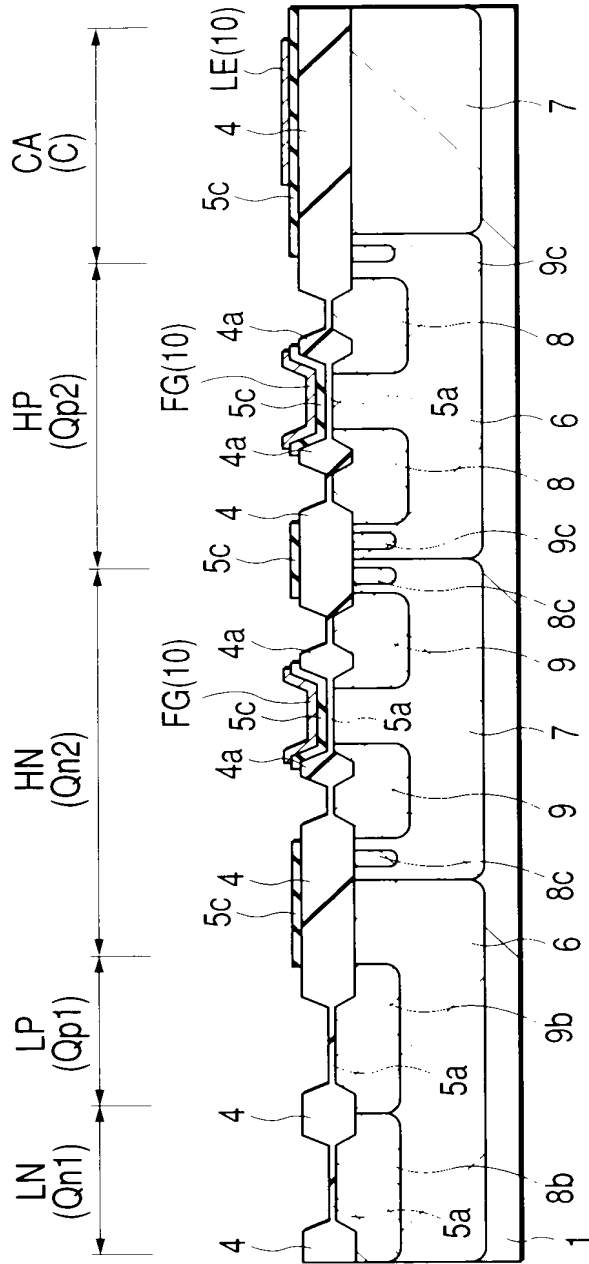


FIG. 35

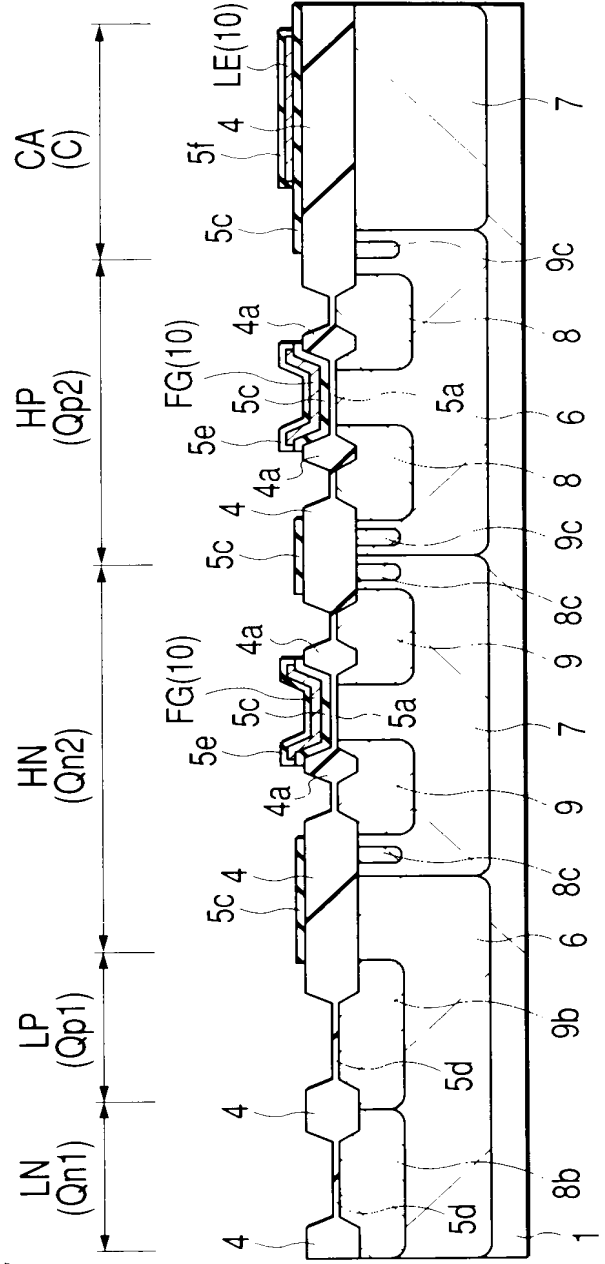


FIG. 36

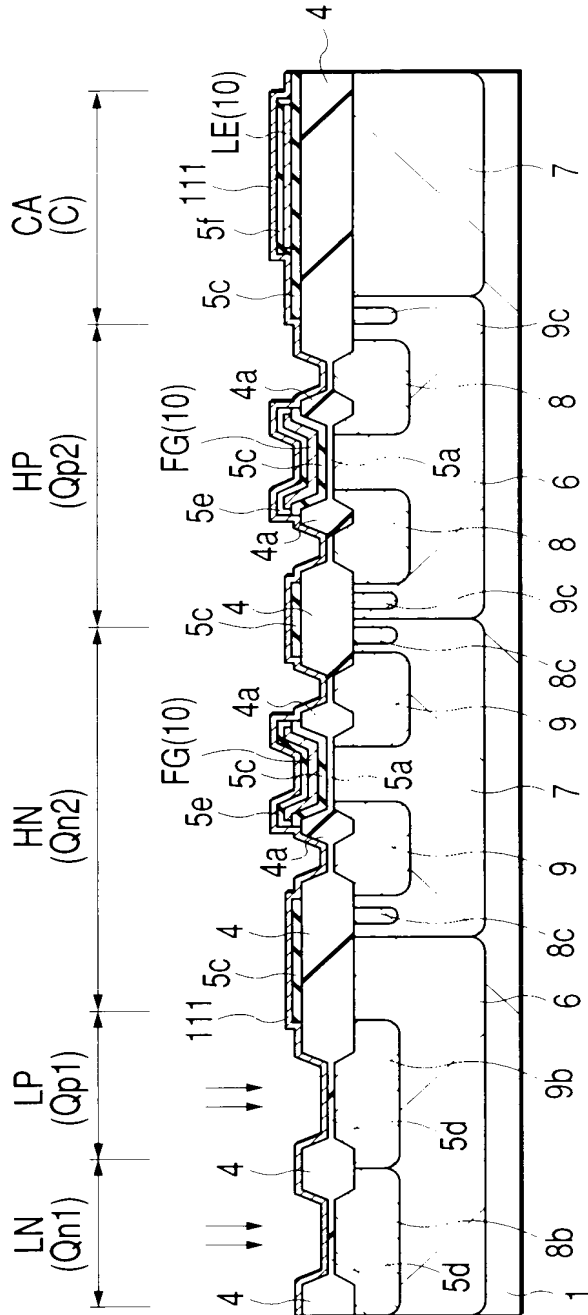


FIG. 37

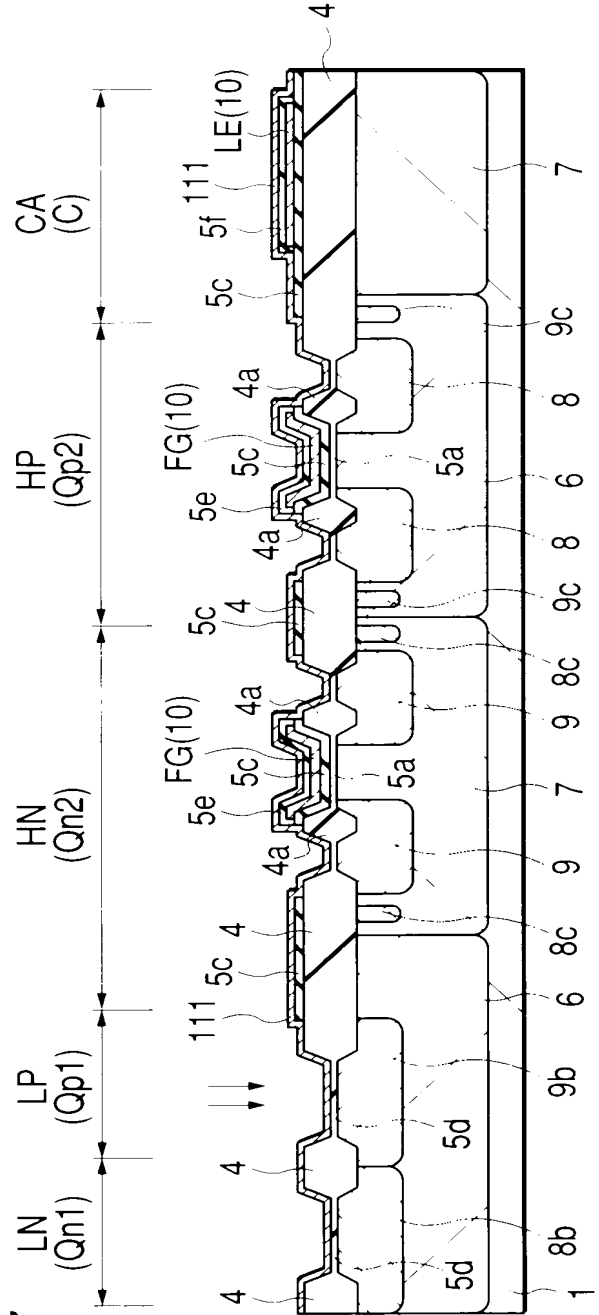


FIG. 38

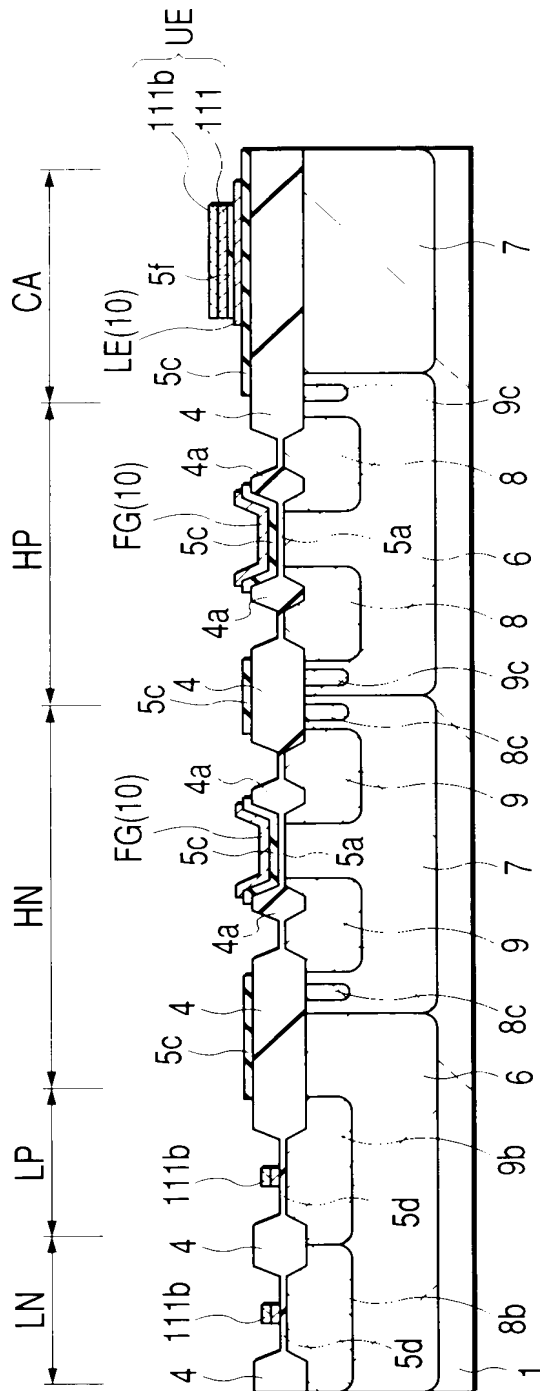
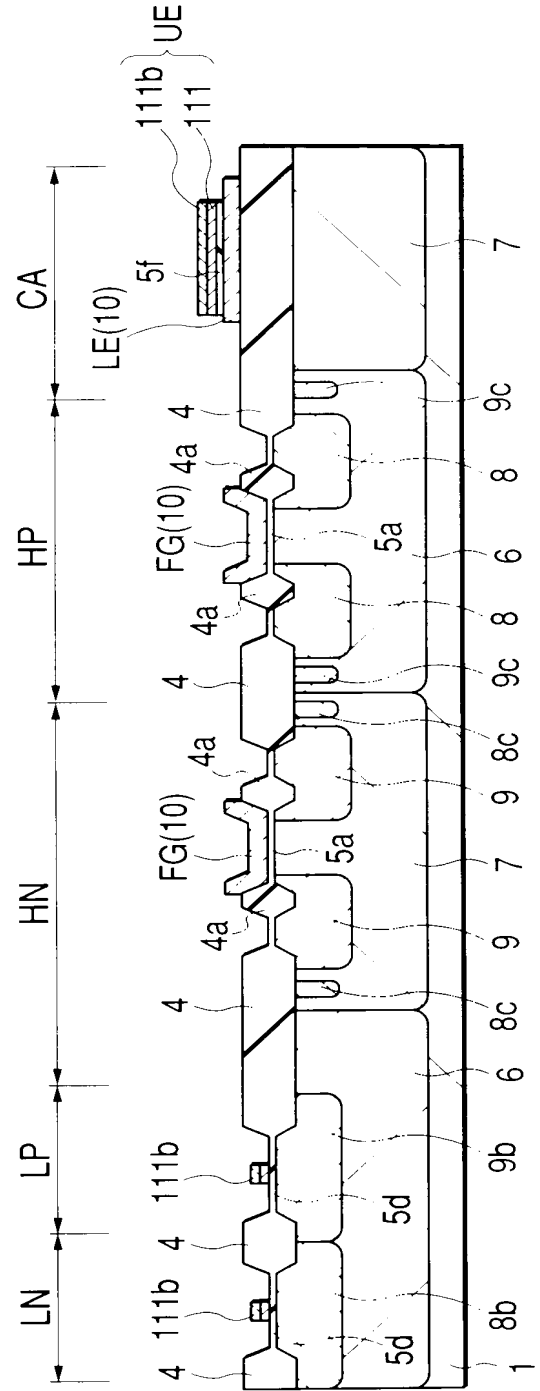
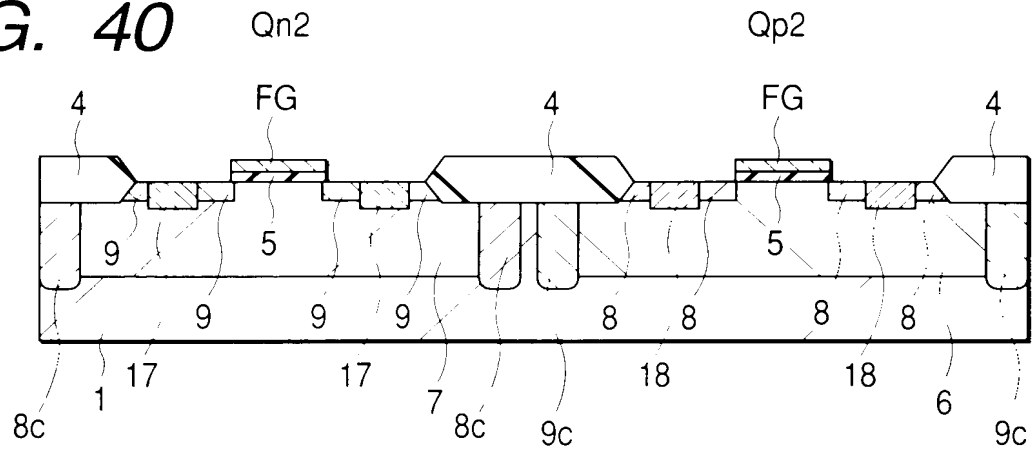


FIG. 39

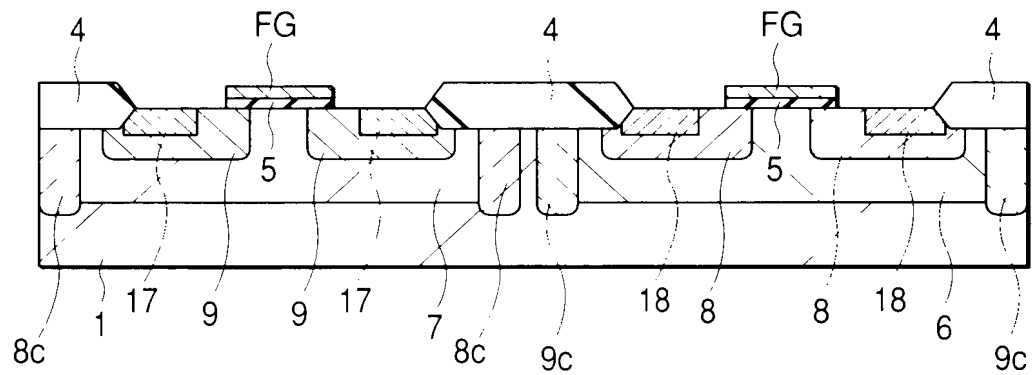




**FIG. 40**



**FIG. 41**



**FIG. 42**

